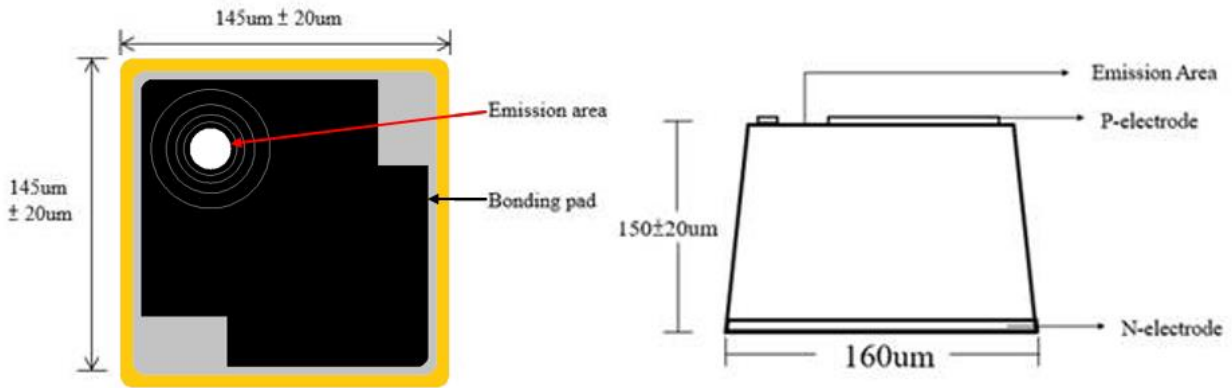


■ Features & Applications :

- 940 nm Wavelength
- Low Dependence of Electrical and Optical Characteristics over Temperature
- Optical Sensing

■ Outline Dimensions : (Unit: μm)



■ Physical Structure :

Chip dimension	Chip size	160 μm x 160 μm
	Thickness	150 \pm 20 μm
Electrode	N(cathode)	Gold
	P (anode)	Gold

■ Electro-Optical Characteristics :

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Output Power	P_o	IF = 10 mA	3	3.8	5	mW
Forward Voltage	VF	IF = 10 mA	1.9	2.0	2.1	V
Threshold Current	I _{th}	-	0.5	1.4	3.0	mA
Wavelength	λ_p	IF = 10 mA	930	940	950	nm
Beam Divergence (1/e ²)	θ	IF = 10 mA	-	14	-	degree

■ Typical Electro-Optical Characteristics Curve:

